

一、 / Descriptions

SOT-89 NPN Silicon NPN transistor in a SOT-89 Plastic Package.

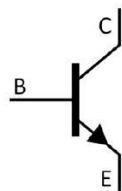
二、 / Features

1、 , 2SB1386
Low $V_{CE(sat)}$, excellent DC current gain , complements the 2SB1386.

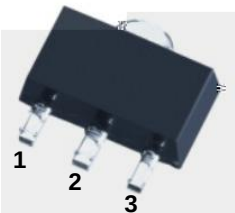
三、 / Applications

Strobe flash applications, general power amplifier applications.

四、 / Equivalent Circuit



五、 / Pinning



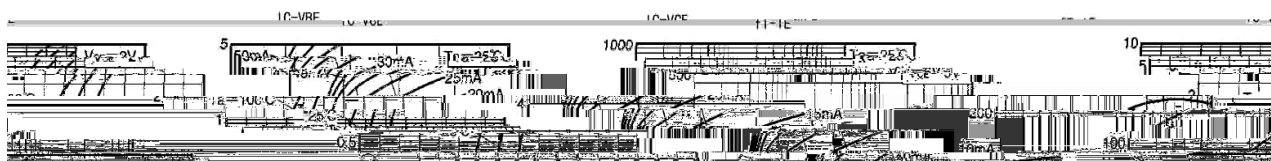
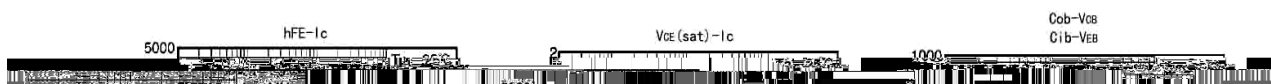
PIN1 Base PIN 2 Collector PIN 3 Emitter

六、 / Marking

h_{FE} Classifications Symbol	Q	R
h_{FE} Range	120 270	180 390
Marking	HAHQ ‡	HAHR ‡

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current-Continuous	I_C	5.0	A
Collector Current -Continuous(Pulse)	I_{CP}	10	A
Collector Power Dissipation	P_C	0.5	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

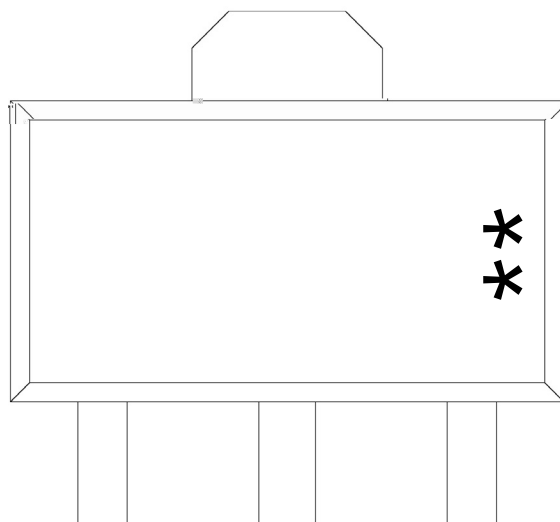
电气特性 / Electrical Characteristic Curve



⌘ È Ò Ì f / Package Dimensions



1. 1.1 / Marking Instructions



H

AH

Q h_{FE}

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Note:

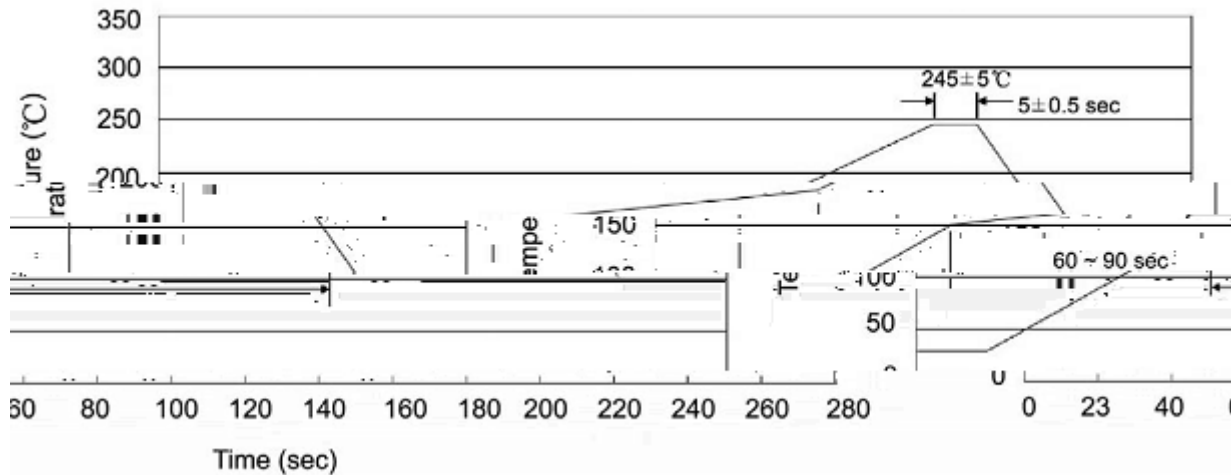
H: Company Code.

AH: Product Type.

Q h_{FE} Classifications Symbol

**: Lot No. Code, code change with Lot No.

Whp shudwxuh Suriloh i ru LU Uhior z Vroghulq j+Se0l uhh,



Note:

- | | | | | | |
|---|-------|-----|-----------|---|--------------------------------------|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. | |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-89	1,000	7	7,000	8	56,000	7 ×12	180×120×180	385×257×392

Notices